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APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/836,426	04/17/2001		Tim Dyer	35013.4000	6845	
7	590	01/21/2003				
Snell & Wilm			EXAMINER			
One Arizona C 400 E. Van Bu	ren Street		MCDONALD, SHANTESE L			
Phoenix, AZ	85004-22	02		ART UNIT	PAPER NUMBER	
				3723		
				DATE MAILED: 01/21/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No. 09/836,426

Applicant(s)

Dyer et al.

Examiner

McDonald, Shantese

Art Unit **3723**



	The MAILING DATE of this communication appears	on the cover she	et with	the correspondence address			
	or Reply		_				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.							
- Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the							
_	date of this communication. Period for reply specified above is less than thirty (30) days, a reply within th	ne statutory minimum d	of thirty (30) days will be considered timely.			
-	eriod for reply is specified above, the maximum statutory period will apply a to reply within the set or extended period for reply will, by statute, cause th	•		•			
- Any rej	ply received by the Office later than three months after the mailing date of the patent term adjustment. See 37 CFR 1.704(b).						
Status	patent term adjustment. 300 37 GHT1.704(g).						
1) 💢	Responsive to communication(s) filed on Oct 22, 20	002		·			
2a) 🗌	This action is FINAL . 2b) 💢 This action	ion is non-final.					
3) 🗆	Since this application is in condition for allowance e closed in accordance with the practice under Ex pair						
Disposit	tion of Claims						
4) 💢	Claim(s) 1-33			is/are pending in the application.			
4	a) Of the above, claim(s)			is/are withdrawn from consideration.			
5) 🗆	Claim(s)			is/are allowed.			
6) 💢	Claim(s) <u>1-33</u>			is/are rejected.			
7) 🗆	Claim(s)			is/are objected to.			
8) 🗌	Claims	are	subject	to restriction and/or election requirement.			
Applica	tion Papers						
9) 🗆	The specification is objected to by the Examiner.						
10)	The drawing(s) filed on is/are	a) accepted	d or b)	\Box objected to by the Examiner.			
	Applicant may not request that any objection to the de	rawing(s) be held	d in abey	vance. See 37 CFR 1.85(a).			
11)	The proposed drawing correction filed on	is:	a) 🗌 a	pproved b) \square disapproved by the Examiner.			
	If approved, corrected drawings are required in reply t	to this Office act	ion.				
12)	The oath or declaration is objected to by the Exami	ner.					
Priority	under 35 U.S.C. §§ 119 and 120						
13) 🗆	Acknowledgement is made of a claim for foreign pr	riority under 35	U.S.C.	§ 119(a)-(d) or (f).			
a) 🗆] All b)□ Some* c)□ None of:						
	1. \square Certified copies of the priority documents have	e been received	i.				
:	2. \square Certified copies of the priority documents have	e been received	in App	lication No			
;	 Copies of the certified copies of the priority do application from the International Burea 	ocuments have au (PCT Rule 17	been re 7.2(a)).	ceived in this National Stage			
*Se	ee the attached detailed Office action for a list of the	e certified copie	s not re	eceived.			
14) 🗆	Acknowledgement is made of a claim for domestic	priority under 3	35 U.S.(C. § 119(e).			
a) L	3						
15)∟	Acknowledgement is made of a claim for domestic	priority under 3	35 U.S.(C. §§ 120 and/or 121.			
Attachm		🗖					
	tice of References Cited (PTO-892)			-413) Paper No(s)			
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 5) Notice of Informal Patent Application (PTO-152) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s). 6) Other:							
3,	America disclosure statement(s) (FTO-1445) Paper NO(8).	o, Li other:					

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-9,26-29, 32 and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lougher et al. in view of Jeng.

Lougher et al. teaches a platen, 211, configured to orbit, (col. 5, lines 46-52), a polishing surface, 108, attached to the platen, a workpiece carrier, 110 and channels in the platen configured to allow polishing solution to circulate through, (col. 5, lines 29-34). Lougher et al. teaches all the limitations of the claims except for the wafer including a low-k material, the platen orbiting about an axis at a speed of about 500 to 2000 revolutions per minute, the platen rotating with an orbital radius of about 0.25 to 1 inch, the carrier and the platen being configured to move the workpiece relative the polishing surface at about 0.8 to 3.2 meters per second, the carrier being configured to apply about 0.25 to 2 pounds per square inch of pressure to the workpiece, allowing the polishing slurry to flow at a rate of about 120 to 200 milliliters per minute. Jeng teaches a wafer comprising low-k material, 18. It would have been obvious to one having ordinary skill in the art at the time the invention was made, to provide the invention of Lougher et

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al. with a wafer comprising low-k material, as taught by Jeng, in order to enhance the range of the machines polishing capabilities. It would have been further obvious to one having ordinary skill in the art at the time the invention was made to make the invention of Lougher et al. with the above listed limitation, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art.

3. Claim 10 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lougher et al. as modified by Jeng as applied to claims 1-9, 26-29, 32 and 33 above, and further in view of Chen et al.

Lougher et all teaches all the limitations of the claims except for the carrier including a bladder to regulate pressure applied to the workpiece. Chen et al. teaches a bladder, 144. It would have been obvious to one having ordinary skill in the art at the time the invention was made, to provide the carrier of Lougher et al. with a bladder, in order to more efficiently regulate the pressure applied to the workpiece.

4. Claims 11, 30 and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lougher et al as modified by Jeng as applied to claims 1-9, 26-29, 32 and 33 above, and further in view of Kawamoto et al.

Lougher et al. teaches all the limitations of the claims except for the platen including a conduit configured to allow heat exchange fluid to flow through, thereby regulating the temperature of the polishing surface and the polishing fluid. Kawamoto et al. teach a conduit configured to allow heat exchange fluid to flow through, (col. 4, lines 25-36). It would have been

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obvious to one having ordinary skill in the art at the time the invention was made, to provide the platen of Lougher et al. with a conduit to allow heat exchange fluid to flow through, as taught by Kawamoto et al. in order to enhance the temperature control of the polishing apparatus.

5. Claims 12-17, 20 and 25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chen et al. in view of Aizawa in further view of Jeng

Chen et al. teaches a plurality of polishing stations, 25, a platen, 30, a load station, 27, a carousel, 60, including a plurality of workpiece carriers, configured to rotate about an axis and translate in a radial direction, (col. 4, lines 16-20). Chen et al. teaches all the limitations of the claims except for a wafer comprising a low-k material, a clean system, a buff station, the platen being configured to move at about 0.8 to 3.2 meters per second relative to the wafer surface, the carrier being configured to apply about 0.25 to 2 pounds per square inch of pressure to the workpiece, the platen being configured to orbit with a radius of about 0.25 to about 1 inch, and the platen being configured to orbit about an axis at a speed of about 500 to 2000 revolutions per minute. Jeng teaches a wafer comprising a low-k material, 18. Aizawa et al. teaches a clean station, 26a, 26b, 26c, and a buffing station, 200. It would have been obvious to one having ordinary skill in the art at the time the invention was made, to make the invention of Chen et al. with a clean station and buffing station, as taught by Aizawa et al., and a wafer comprising a lowk material, as taught by Jeng, in order to enhance the machines polishing capabilities. It would have been further obvious to make the invention of Chen et al. as modified by Aizawa et al. with the limitations state above, since it has been held that where the general conditions of a claim are

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disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art.

6. Claims 18, 19, 22 and 24 rejected under 35 U.S.C. 103(a) as being unpatentable over Chen as modified by Aizawa and Jeng as applied to claims 12-17, 20 and 25 above, and further in view of Lougher et al.

Chen as modified by Aizawa teaches all the limitations of the claims except for a platen configured to orbit, with channels to allow polishing fluid to flow through and a polishing surface which allows the polishing fluid to circulate through a portion of the polishing surface. Lougher et al. teaches a platen configured to orbit, (col. 5, lines 46-52), and channels in the platen and polishing pad which allow the polishing fluid to flow through, (col. 5, lines 29-34). It would have been obvious to one having ordinary skill in the art at the time the invention was made, to provide the apparatus of Chen as modified by Aizawa, with the orbiting platen and channels in the platen and polishing pad, as taught by Lougher et al., in order to enhance the polishing capabilities.

7. Claims 21 and 23 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chen as modified by Aizawa and further in view of Kawamoto et al.

Chen as modified by Aizawa teaches all the limitations of the claims except for a temperature control system and the platen allowing heat exchange fluid to flow through. Kawamoto et al. teach a platen configured to allow heat exchange fluid to flow through, thereby regulating the temperature of the polishing fluid, (col. 4, lines 25-36). It would have been obvious to one having ordinary skill in the art at the time the invention was made, to provide the Art Unit: 3723

platen of Chen as modified by Aizawa with a platen to allow heat exchange fluid to flow through, as taught by Kawamoto et al. in order to enhance the temperature control of the polishing apparatus.

Response to Arguments

- 8. Applicant's arguments filed 10/22/02 have been fully considered but they are not persuasive. The applicant argues that the rejection made on 8/1/02, is not valid because the references do not teach or suggest a method or an apparatus for polishing a surface of a workpiece comprising low-k material. The Examiner has applied a reference which teaches that the wafer comprises a low-k material.
- 9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shantese McDonald whose telephone number is (703) 308-8722.

Joseph J. Hail, III Supervisory Patent Examiner Technology Center 3700

S.L.M.